

Description

The HXY3422MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

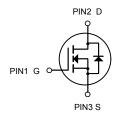
D G SOT23-3L

General Features

 $V_{DS} = 60V, I_{D} = 4.5A$

 $R_{DS(ON)} < 75m\Omega$ @ $V_{GS}=10V$

 $R_{DS(ON)}$ < 90m Ω @ V_{GS} =4.5V



N-Channel MOSFET

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3422MI	SOT23-3L	ARDP 7B	3000PCS

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _D s	Drain-Source Voltage	60	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	4.5	А
Ідм	Drain Current-Pulsed (Note 1)	15	А
P _D	Maximum Power Dissipation	8	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Rеja	Thermal Resistance, Junction-to-Ambient (Note 2)	89	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
Process	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =5A		70	75	0
R _{DS(ON)}		V _{GS} =4.5V , I _D =5A		80	90	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
1	Durin Course Landson Course	V _{DS} =48V , V _{GS} =0V , T _J =25°C			1	- uA
IDSS	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =55°C			5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =5A		7		S
Qg	Total Gate Charge (10V)			5.5		
Q _{gs}	Gate-Source Charge	V _{DS} =12V , V _{GS} =10V , I _D =5A		1.8		nC
Q_{gd}	Gate-Drain Charge			2.4		
T _{d(on)}	Turn-On Delay Time			6		
Tr	Rise Time	V_{DD} =12V , V_{GS} =10V , R_{G} =3.3 Ω		10		
T _{d(off)}	Turn-Off Delay Time	I _D =5A		15		ns
T _f	Fall Time			7		
Ciss	Input Capacitance			695		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		148		pF
Crss	Reverse Transfer Capacitance			7		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,5}	V- V- OV Force Current			17	Α
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			50	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.1 mH, I_{AS} =15A

^{4.}The power dissipation is limited by 150°C junction temperature

^{5.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

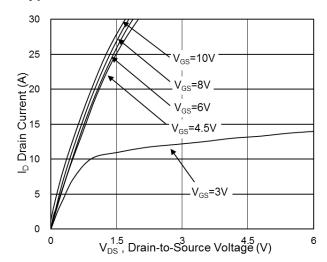


Fig.1 Typical Output Characteristics

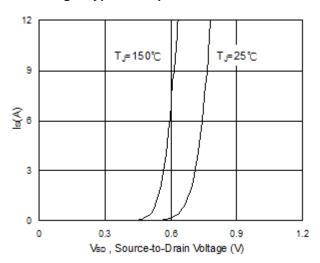


Fig.3 Forward Characteristics of Reverse

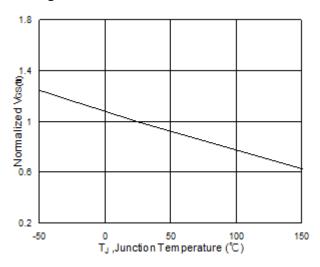


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

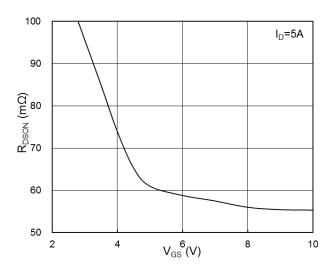


Fig.2 On-Resistance vs. Gate-Source Voltage

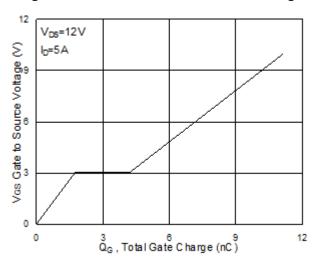


Fig.4 Gate-Charge Characteristics

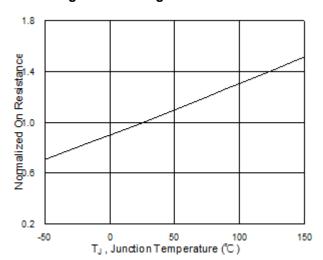
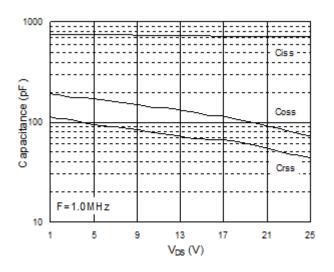


Fig.6 Normalized R_{DSON} vs. T_J





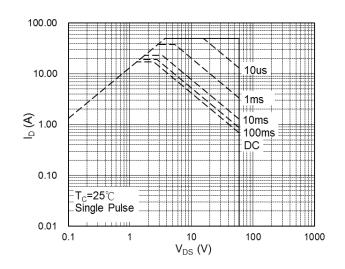


Fig.7 Capacitance

Fig.8 Safe Operating Area

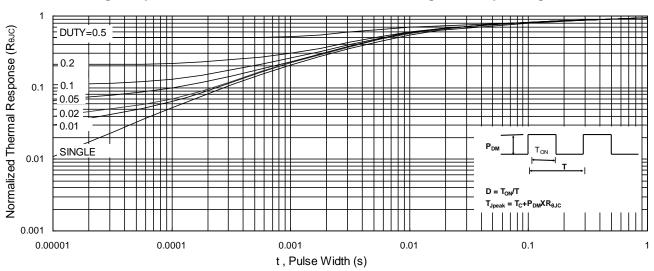


Fig.9 Normalized Maximum Transient Thermal Impedance

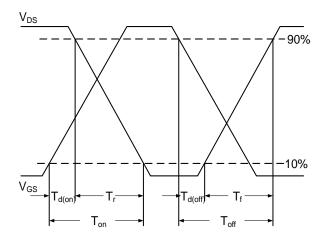


Fig.10 Switching Time Waveform

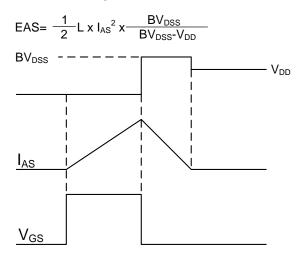
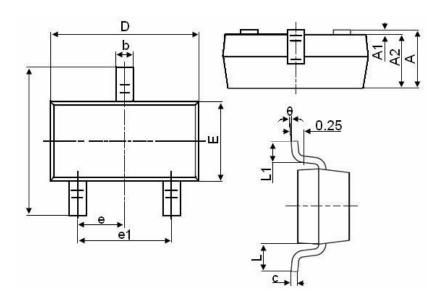


Fig.11 Unclamped Inductive Switching Waveform



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
Е	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

 HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by HXY MOS manufacturer:

Other Similar products are found below:

MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ NTNS3A92PZT5G IRFD120 JANTX2N5237 2N7000 2SK2464-TL-E AOD464 2SJ277-DL-E 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C IRS2092STRPBF-EL IPS70R2K0CEAKMA1 BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6 C3M0021120D DMN6022SSD-13